

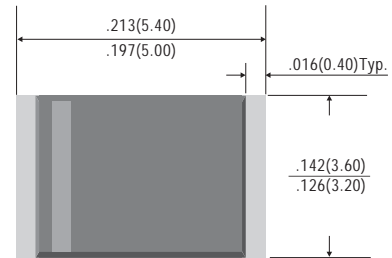


### Features

- Batch process design, excellent power dissipation offers better reverse leakage current and thermal resistance.
- Low profile surface mounted application in order to optimize board space.
- Tiny plastic SMD package.
- $t_{rr}$  less than 25ns for high efficiency
- High current & surge capability.
- Low forward dropdown voltage
- Glass passivated chip junction.
- **Moisture Sensitivity Level 1**

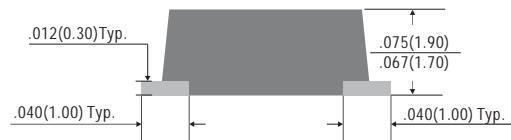
### Package outline

SMB-L



### Mechanical data

- Epoxy:UL94-V0 rated flame retardant
- Case : Molded plastic, SMB-L
- Terminals : Solder plated, solderable per MIL-STD-750, Method 2026
- Polarity : Indicated by cathode band
- Mounting Position : Any
- Weight : Approximated 0.09 gram



Dimensions in inches and (millimeters)

### Maximum ratings and Electrical Characteristics (AT $T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	CONDITIONS	Symbol	MIN.	TYP.	MAX.	UNIT
Forward rectified current	See Fig.2	$I_o$			2.0	A
Forward surge current	8.3ms single half sine-wave superimposed on rate load (JEDEC methode)	$I_{FSM}$			50	A
Reverse current	$V_R = V_{RRM} T_J = 25^\circ\text{C}$	$I_R$			5.0	$\mu\text{A}$
	$V_R = V_{RRM} T_J = 125^\circ\text{C}$				100	
Diode junction capacitance	f=1MHz and applied 4V DC reverse voltage	$C_j$		50		pF
Storage temperature		$T_{STG}$	-55		+150	$^\circ\text{C}$

SYMBOLS	$V_{RRM}^{*1}$ (V)	$V_{RMS}^{*2}$ (V)	$V_R^{*3}$ (V)	$V_F^{*4}$ (V)	$t_{rr}^{*5}$ (ns)	Operating temperature $T_J, (^\circ\text{C})$
WØT GŠ	50	35	50	0.875	25	-55 to +150
WØT GGŠ	100	70	100			
WØT G Š	200	140	200			
UFM26L	400	280	400	1.25		
WFM2ì Š	600	420	600	1.75		

Note 1. Reverse recovery time test condition,  $I_F=0.5\text{A}$ ,  $I_R=1.0\text{A}$ ,  $I_{RR}=0.25\text{A}$

- \*1 Repetitive peak reverse voltage
- \*2 RMS voltage
- \*3 Continuous reverse voltage
- \*4 Maximum forward voltage@ $I_F=2.0\text{A}$
- \*5 Reverse recovery time, note 1

Rating and characteristic curves

FIG.1-TYPICAL FORWARD CHARACTERISTICS

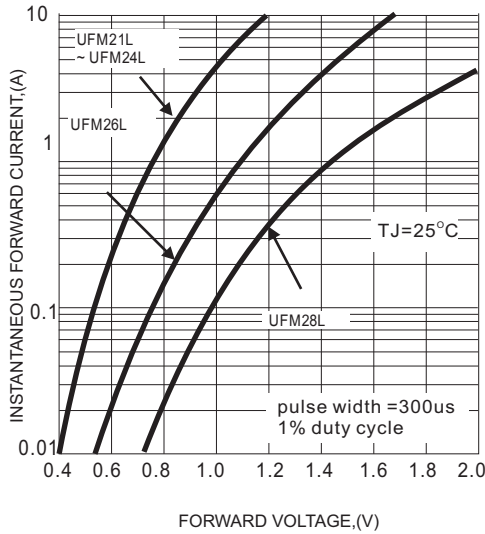


FIG.2-TYPICAL FORWARD CURRENT DERATING CURVE

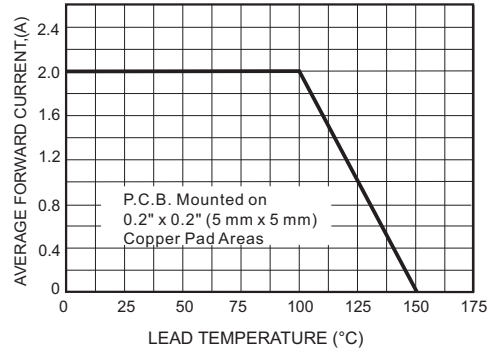
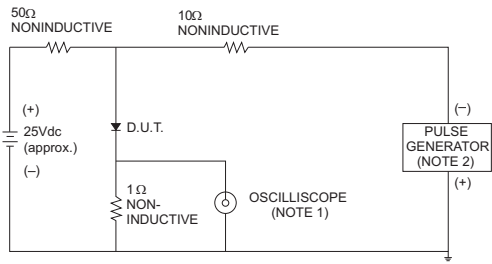


FIG.3- TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTICS



NOTES: 1. Rise Time= 7ns max., Input Impedance= 1 megohm. 22pF.  
2. Rise Time= 10ns max., Source Impedance= 50 ohms.

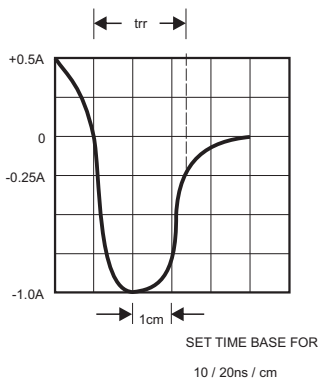


FIG.4-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

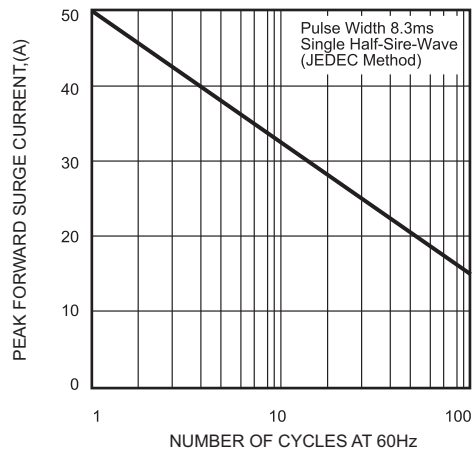
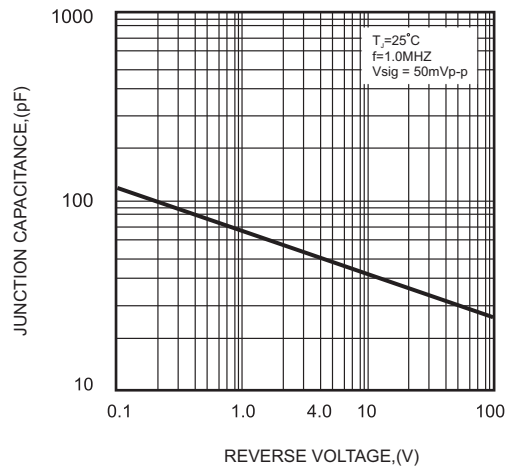


FIG.5-TYPICAL JUNCTION CAPACITANCE





### Pinning information

Pin	Simplified outline	Symbol
Pin1 cathode Pin2 anode		

### Reel packing

PACKAGE	REEL SIZE	REEL (pcs)	COMPONENT SPACING (m/m)	BOX (pcs)	INNER BOX (m/m)	REEL DIA, (m/m)	CARTON SIZE (m/m)	CARTON (pcs)	APPROX. GROSS WEIGHT (kg)
SMB-L	13"	4,000	8.0	8,000	337*337*37	330	350*330*360	64,000	16.9

### Marking

Type number	Marking code
UFM21L-TH	E21
UFM22L-TH	E22
UFM24L-TH	E23
UFM26L-TH	E24
UFM28L-TH	E25

Note: L: Package code, SMB-L

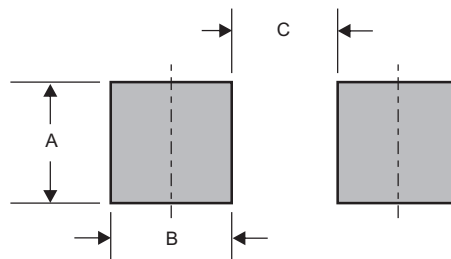
-T: Taping Reel

**Pb-Free package is available**

RoHS product for packing code suffix "G"

Halogen free product for packing code suffix "H"

### Suggested solder pad layout

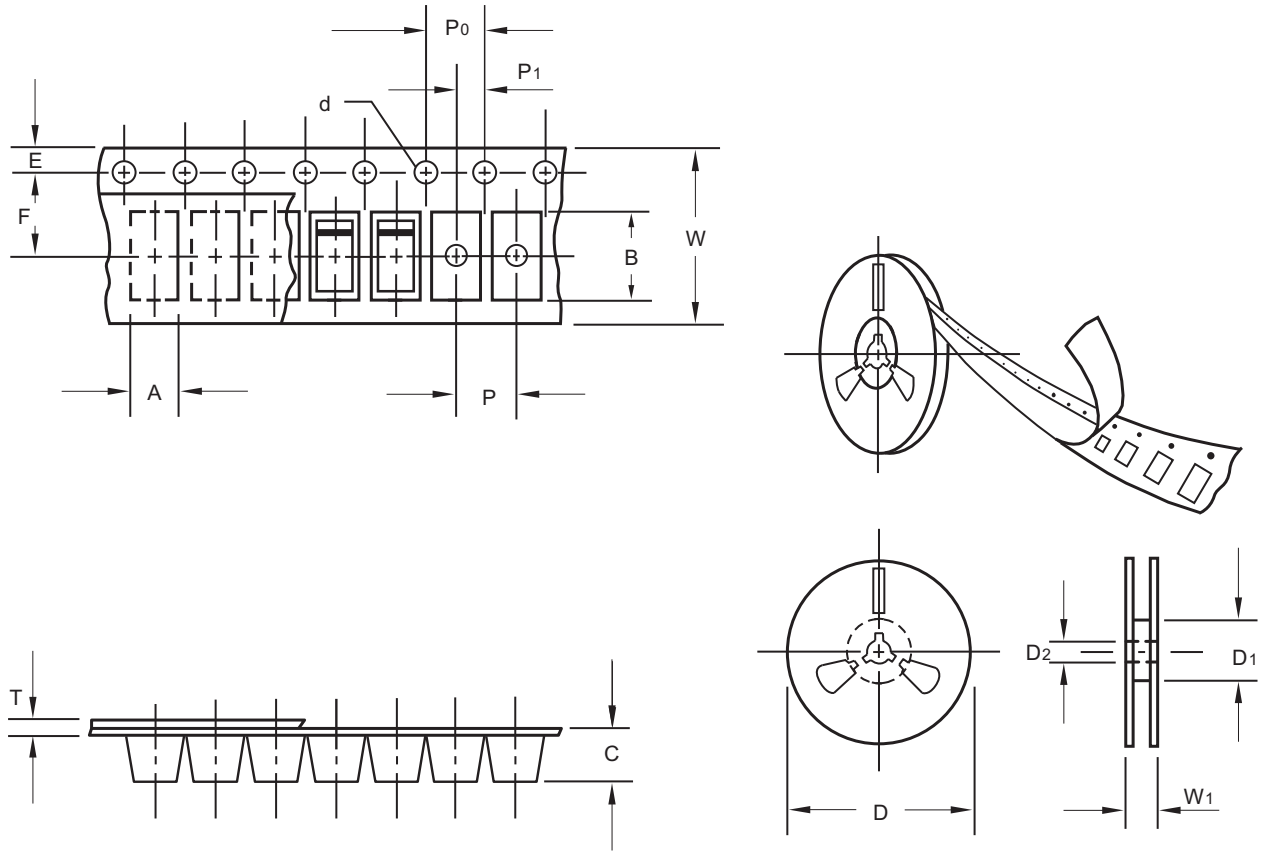


Dimensions in inches and (millimeters)

PACKAGE	A	B	C
SMB-L	0.142 (3.60)	0.059 (1.50)	0.118 (3.00)



### Packing information



unit:mm

Item	Symbol	Tolerance	SMB-L
Carrier width	A	0.1	3.81
Carrier length	B	0.1	5.74
Carrier depth	C	0.1	2.24
Sprocket hole	d	0.1	1.50
13" Reel outside diameter	D	2.0	330.00
13" Reel inner diameter	D1	min	50.00
7" Reel outside diameter	D	2.0	178.00
7" Reel inner diameter	D1	min	62.00
Feed hole diameter	D2	0.5	13.00
Sprocket hole position	E	0.1	1.75
Punch hole position	F	0.1	5.50
Punch hole pitch	P	0.1	8.00
Sprocket hole pitch	P0	0.1	4.00
Embossment center	P1	0.1	2.00
Overall tape thickness	T	0.1	0.23
Tape width	W	0.3	12.00
Reel width	W1	1.0	18.00

Note: Devices are packed in accordance with EIA standard RS-481-A and specifications listed above.